

REMARKS

Entry of this amendment prior to examination is respectfully requested.

By the present amendment, the Continuation information, required under 37 CFR § 1.72 is provided.

The present Continuation application presents claims 1-6 for examination. These claims are similar to claims 1-6 of the parent application in the form that they were presented in the August 12, 2002 Amendment in the parent case serial number 09/715,105. In the parent application, claims 1, 3, and 5 were amended based upon discussions with the Examiner, to include further limitations regarding the polycrystalline silicon semiconductor layer being formed on a substrate of a stack of recrystallized semiconductor layers. This limitation in the parent application served to distinguish the claims of the parent application further over U.S. Patent 6,335,542 to Miyasaka. However, upon further review of this matter, it is respectfully submitted that claims 1-6, presented in the present Continuation application, patentably define over the Miyasaka patent without the need for the limitation which was added by the Examiner's amendment in the parent case. Accordingly, consideration of claims 1-6 submitted herewith in light of the following comments is respectfully requested.

More specifically, the Miyasaka patent states that a semiconductor film thickness of 5% or less can be provided. This is discussed, for example, in connection with the explanation of Fig. 5 of Miyasaka. However, in Miyasaka, the semiconductor films in question are amorphous semiconductor films. Therefore, Miyasaka fails to teach or suggest the features set forth in claims 1-6 regarding unevenness of the surface of a polysilicon film.

With regard to this, in Miyasaka amorphous semiconductor films are molten and recrystallized into polysilicon films. During this conversion process into polysilicon film, the surface of the polysilicon film which results from the conversion

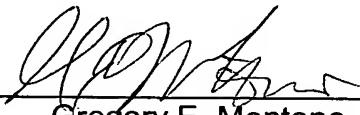
will tend to become uneven. However, Miyasaka fails to teach or suggest the degree of unevenness resulting polysilicon film. As such, it is respectfully submitted that Miyasaka fails to teach or suggest the specific claim limitations such as found in independent claims 1, 3, and 5 that the unevenness of the surface of the polycrystalline silicon semiconductor layer is within 10% of the thickness of the polycrystalline silicon semiconductor layer. Accordingly, reconsideration and allowance of claims 1-6 presented with this Continuation application is earnestly solicited.

In view of the foregoing, entry of the present amendments and examination of the above-identified application on the merits in due course, are respectfully requested.

Kindly charge any additional fees due, or credit overpayment of fees, to Deposit Account No. 01-2135 (520.39294CX1).

Respectfully submitted,

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